

General Description

GL30J50BN the silicon N-channel Enhanced VDMOSFETS, is obtained by the self-aligned Super-junction Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-3P(N), which accords with the RoHS standard.

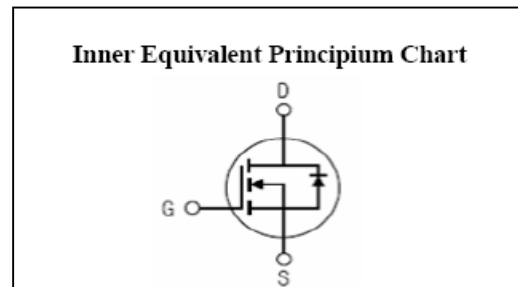
Features

- Fast Switching
- Low Gate Charge and $R_{ds(on)}$
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction(PFC)

V_{DSS}	500	V
I_D	30	A
$P_D(T_C=25^{\circ}C)$	166	W
$R_{DS(ON)TYP}$	86	m Ω



Absolute ($T_C = 25^{\circ}C$ unless otherwise specified) :

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	500	V
I_D	Continuous Drain Current	30	A
I_{DM}^{a1}	Pulsed Drain Current	120	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	480	mJ
P_D	Power Dissipation	151	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^{\circ}C$
T_L	Maximum Temperature for Soldering	300	$^{\circ}C$

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	0.83	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-Ambient	62	$^{\circ}C/W$



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Electrical Characteristics (Tc= 25°C unless otherwise specified)

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	500	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=500V, V_{GS}=0V, T_a=25^\circ C$	--	--	1.0	μA
		$V_{DS}=400V, V_{GS}=0V, T_a=150^\circ C$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}^{a3}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=15A$	--	86	100	m Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	--	4.0	V

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}^{a3}	Forward Transconductance	$V_{DS}=10V, I_D=15A$	--	18.8	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_D=50V$ $f=1.0MHz$	--	2328	--	pF
C_{oss}	Output Capacitance		--	116	--	
C_{rss}	Reverse Transfer Capacitance		--	7	--	

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=400V, I_D=30A,$ $V_{GS}=10V R_g=25\Omega$	--	43	--	ns
t_r	Rise Time		--	14	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	150	--	
t_f	Fall Time		--	7	--	
Q_g	Total Gate Charge	$I_D=30A, V_{DD}=400V$ $V_{GS}=0 \text{ to } 10V$	--	46	--	nC
Q_{gs}	Gate to Source Charge		--	11	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	13	--	



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Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	30	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	90	A
V_{SD}	Diode Forward Voltage	$I_S=30A, V_{GS}=0V$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=30A, V_{GS}=0V$	--	460	--	ns
Q_{rr}	Reverse Recovery Charge	$I_S=I_F, d_i/d_t=100A/us$	--	3.8	--	uC
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $I_{AS}=4A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$

^{a3}: Pulse Test: Pulse width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Typical Characteristics

Figure 1. Output Characteristics

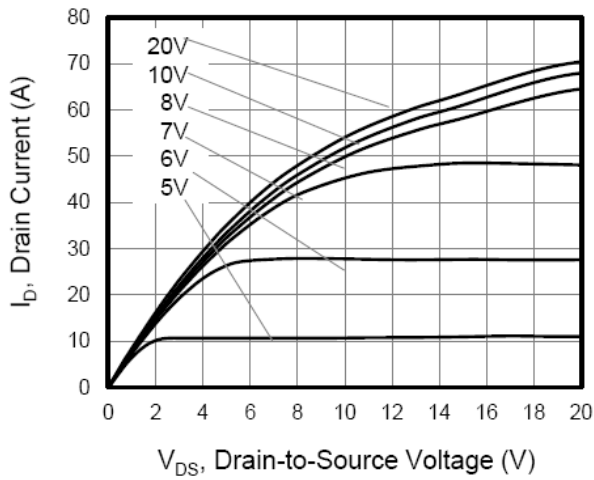


Figure 2. Transfer Characteristics

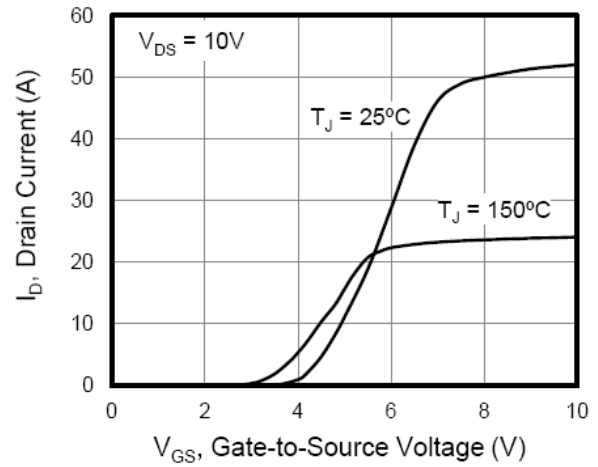


Figure 3. On-Resistance vs. Drain Current

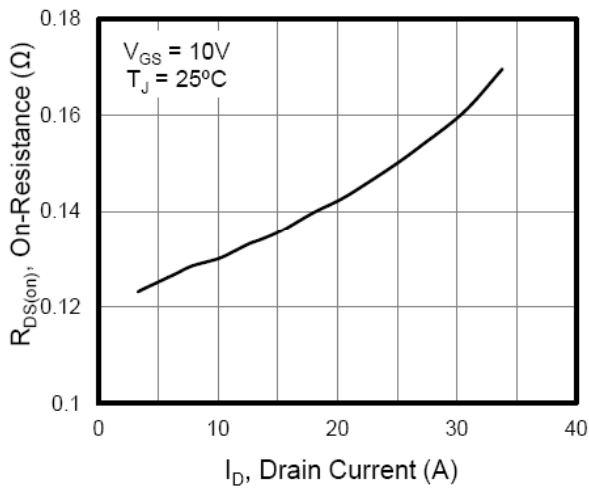


Figure 4. Capacitance

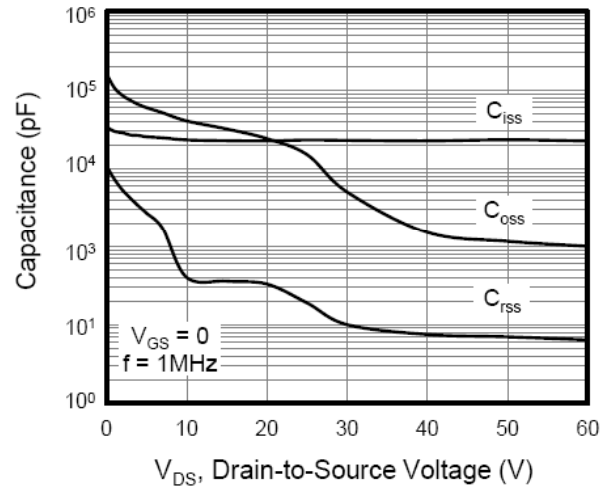


Figure 5. Gate Charge

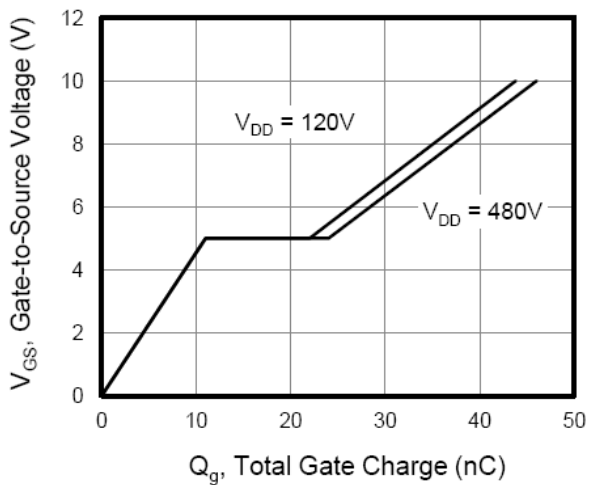
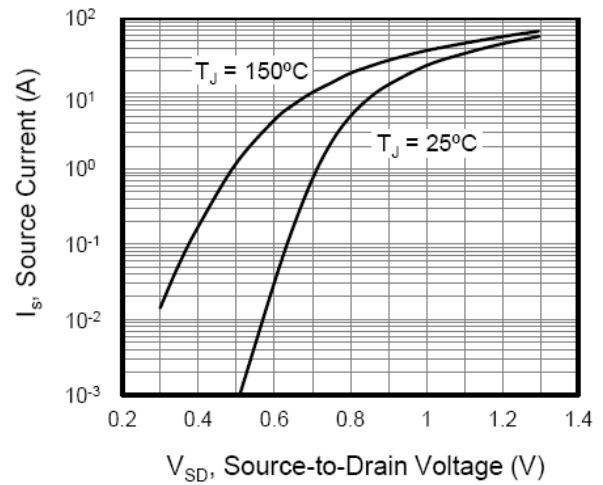


Figure 6. Body Diode Forward Voltage



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Figure 7. On-Resistance vs. Junction Temperature

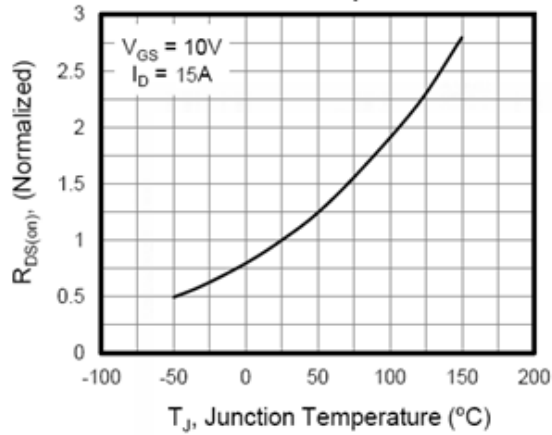


Figure 8. Threshold Voltage vs. Junction Temperature

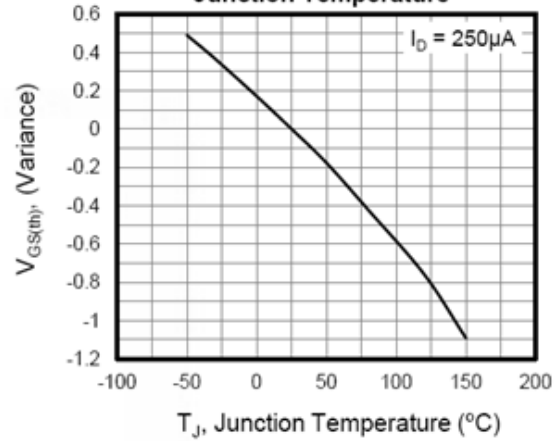


Figure 9. Transient Thermal Impedance TO-220/TO-3P

